[SILICON DIOXIDE REMOVING METHOD]

Abstract

A method for removing silicon dioxide residuals is disclosed. The method includes reacting a portion of a silicon dioxide layer (i.e., oxide) to form a reaction product layer, removing the reaction product layer and annealing in an environment to remove oxide residuals. The method finds application in a variety of semiconductor fabrication processes including, for example, fabrication of a vertical HBT or silicon-to-silicon interface without an oxide interface.